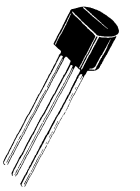
2N5208 (SILICON)

PNP SILICON ANNULAR TRANSISTOR

. . . designed for general purpose RF amplifier applications in the frequency range up to 300 MHz.

- Low Collector-Base Time Constant – r_b 'C_c < 10 ps
- Low Noise Figure N.F. = 3.0 dB max @ 100 MHz
- High Power Gain – G_{pe} = 22 dB min @ 100 MHz
- Complete Y-Parameter Curves
- Low Leakage Current – I_{CBO} < 10 nAdc @ V_{CB} = 10 V
- Stability Factor Curves - For Direct Circuit Design

PNP SILICON SWITCHING AND AMPLIFIER TRANSISTOR



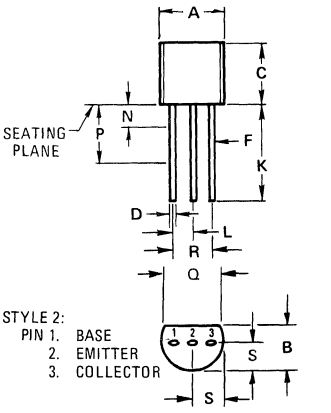
***MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CB}	30	Vdc
Emitter-Base Voltage	V_{EB}	3.0	Vdc
Collector Current – Continuous	I_C	50	mAdc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J,T_{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

*Indicates JEDEC Registered Data.
(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.450	5.200	0.175	0.205
B	3.180	4.190	0.125	0.165
C	4.320	5.330	0.170	0.210
D	0.407	0.533	0.016	0.021
F	0.407	0.482	0.016	0.019
K	12.700	–	0.500	–
L	1.150	1.390	0.045	0.055
N	–	1.270	–	0.050
P	6.350	–	0.250	–
Q	3.430	–	0.135	–
R	2.410	2.670	0.095	0.105
S	2.030	2.670	0.080	0.105

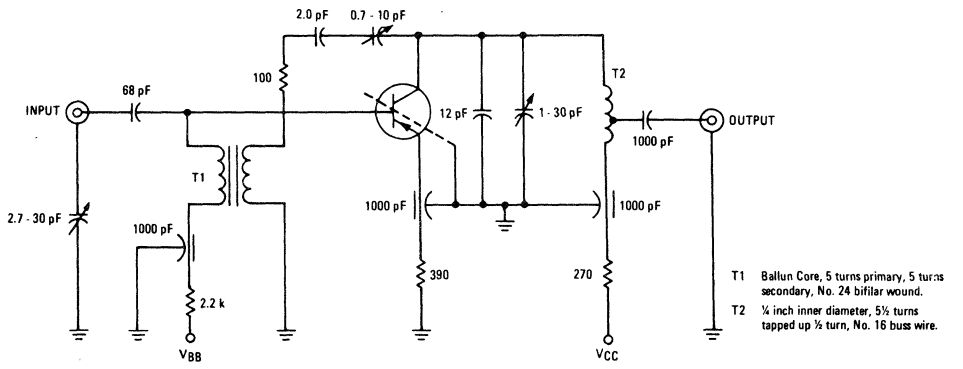
CASE 29-02
TO-92

*ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	BV_{CEO}	25	-	Vdc
Collector-Base Breakdown Voltage (I_C = 0.1 mAdc, I_E = 0)	BV_{CBO}	30	-	Vdc
Emitter-Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	BV_{EBO}	3.0	-	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)	I_{CBO}	-	10	nAdc
Emitter Cutoff Current (V_{BE} = 2.0 Vdc, I_C = 0)	I_{EBO}	-	100	nAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 2.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	20	120	-
Base-Emitter On Voltage (I_C = 2.0 mAdc, V_{CE} = 10 Vdc)	$V_{BE(on)}$	-	0.85	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain—Bandwidth Product (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	300	1200	MHz
Collector-Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	-	1.0	pF
Input Capacitance (V_{BE} = 2.0 Vdc, I_C = 0, f = 1.0 MHz)	C_{ib}	-	4.0	pF
Collector-Base Time Constant (I_E = 2.0 mAdc, V_{CB} = 10 Vdc, f = 31.8 MHz)	$r_b'C_c$	-	10	ps
Noise Figure (See Figure 1) (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, R_S = 75 ohms, f = 100 MHz, BW = 1.0 MHz)	NF	-	3.0	dB
FUNCTIONAL TEST				
Common-Emitter Amplifier Power Gain (See Figure 1) (I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	G_{pe}	22	-	dB

* Indicates JEDEC Registered Data

FIGURE 1 - 100 MHz POWER GAIN AND NOISE FIGURE TEST CIRCUIT



COMMON-EMITTER Y PARAMETERS (Polar Plots)

V_{CE} = 10 Vdc, T_A = 25°C

FIGURE 2 - INPUT ADMITTANCE

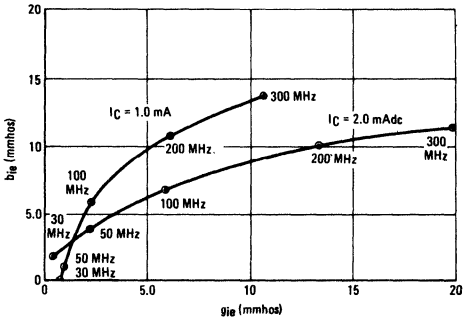


FIGURE 3 - OUTPUT ADMITTANCE

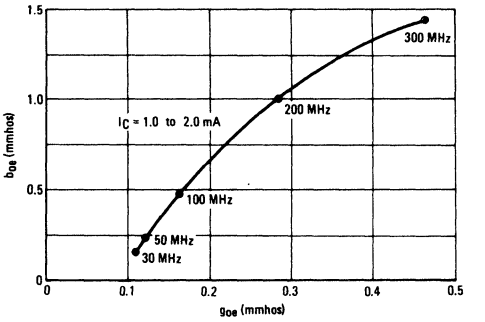


FIGURE 4 - FORWARD TRANSFER ADMITTANCE

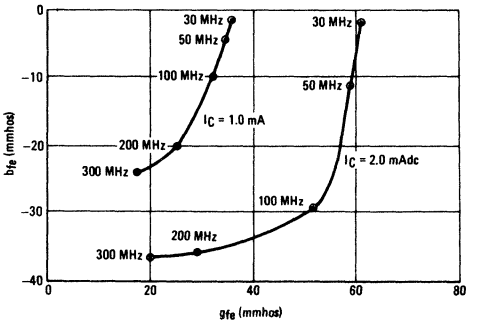
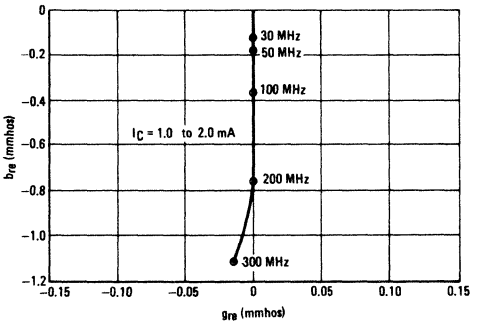


FIGURE 5 - REVERSE TRANSFER ADMITTANCE



STABILITY FACTOR CURVE

FIGURE 6 - POWER GAIN AND NOISE FIGURE

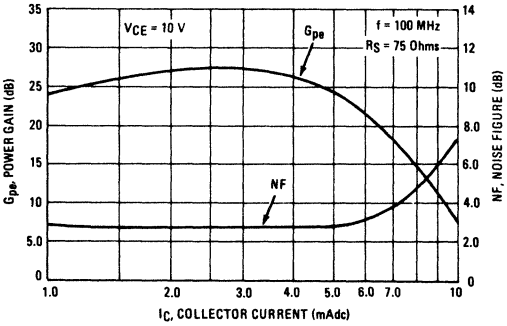
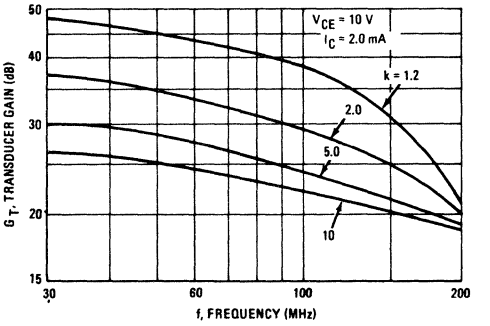


FIGURE 7 - MAXIMUM TRANSDUCER GAIN



COMMON-EMITTER Y PARAMETERS vs FREQUENCY

V_{CE} = 10 Vdc, T_A = 25°C

FIGURE 8 - INPUT ADMITTANCE

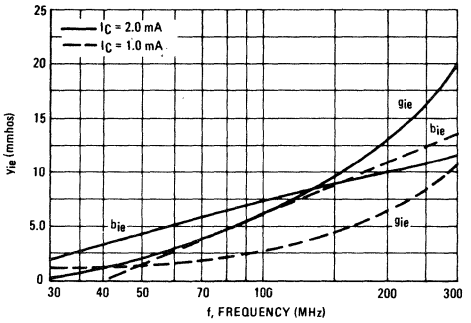


FIGURE 9 - OUTPUT ADMITTANCE

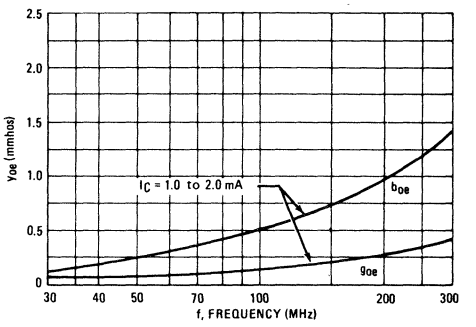


FIGURE 10 - FORWARD TRANSFER ADMITTANCE

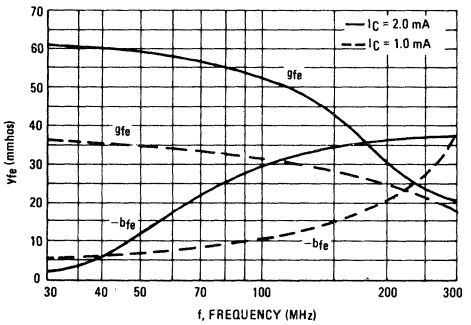
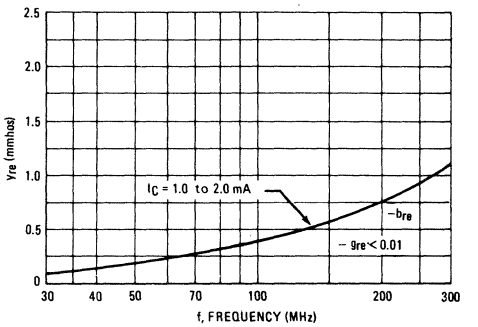


FIGURE 11 - REVERSE TRANSFER ADMITTANCE



STABILITY FACTOR CURVES

FIGURE 12 - OPTIMUM SOURCE ADMITTANCE

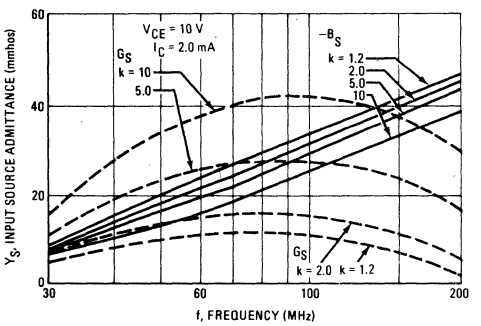
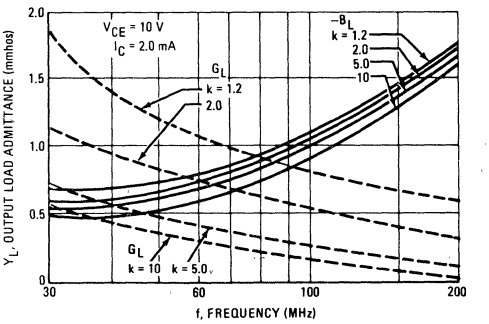


FIGURE 13 - OPTIMUM LOAD ADMITTANCE



When a potentially unstable device is operated without feedback, there is an infinite number of combinations of source and load admittance associated with any given circuit stability factor (k). Equations have been developed for determining the optimum source and load admittance for maximum gain. Figures 7, 12 and 13 provide a solution to the equations for the 2N5208.

NOISE FIGURE

FIGURE 14 - FREQUENCY EFFECTS

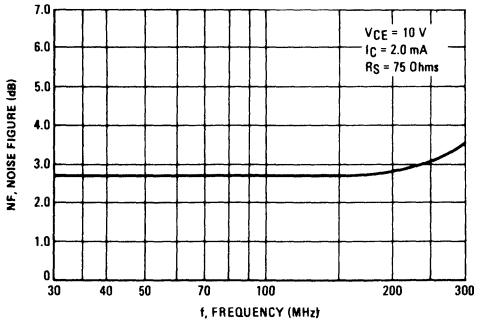


FIGURE 15 - SOURCE RESISTANCE EFFECTS

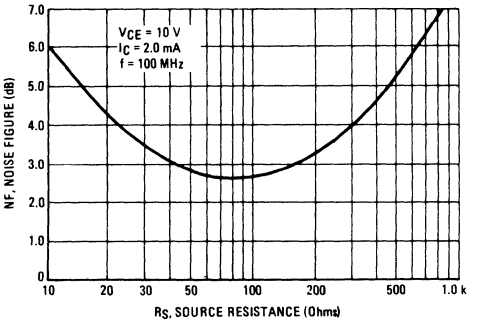


FIGURE 16 - CURRENT-GAIN — BANDWIDTH PRODUCT

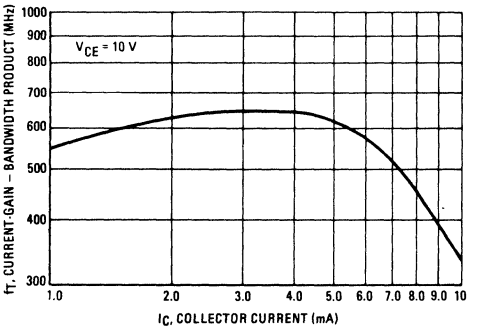


FIGURE 17 - CAPACITANCES

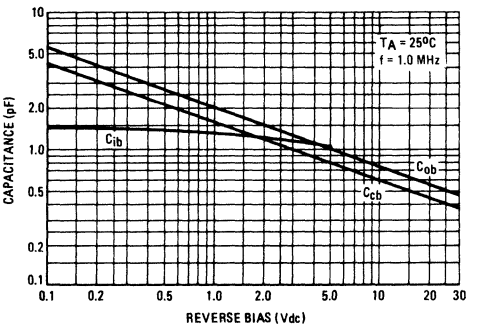


FIGURE 18 - DC CURRENT GAIN